

# Osamu Nakatsuka

## List of Publications by Year in descending order

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250  
papers

3,131  
citations

201385

27  
h-index

214527

47  
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252  
all docs

252  
docs citations

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times ranked

2159  
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoluminescence properties of heavily Sb doped Ge <sub>1-x</sub> Sn <sub>x</sub> and heterostructure design favorable for n <sup>+</sup> -Ge <sub>1-x</sub> Sn <sub>x</sub> active layer. Japanese Journal of Applied Physics, 2022, 61, SA1004.	0.8	1
2	Constructed Ge Quantum Dots and Sn Precipitate SiGeSn Hybrid Film with High Thermoelectric Performance at Low Temperature Region. Advanced Energy Materials, 2022, 12, .	10.2	22
3	Interface Structures and Electrical Properties of Micro-Fabricated Epitaxial Hf-Digermanide/ <i>n</i> -Ge(001) Contacts. IEEE Journal of the Electron Devices Society, 2022, 10, 744-750.	1.2	0
4	Enhancement of channel mobility in 4H-SiC trench MOSFET by inducing stress at SiO <sub>2</sub> /SiC gate interface. Japanese Journal of Applied Physics, 2022, 61, SC1068.	0.8	1
5	Impact of oxide/4H-SiC interface state density on field-effect mobility of counter-doped n-channel 4H-SiC MOSFETs. Japanese Journal of Applied Physics, 2022, 61, 021007.	0.8	3
6	Crystal structure change in multilayer GeH flakes by hydrogen desorption under ultrahigh vacuum environments. Japanese Journal of Applied Physics, 2022, 61, SC1048.	0.8	4
7	Solid-phase crystallization of ultra-thin amorphous Ge layers on insulators. Japanese Journal of Applied Physics, 2022, 61, SC1086.	0.8	2
8	Low-temperature formation of Mg/n-type 4H-SiC ohmic contacts with atomically flat interface by lowering of Schottky barrier height. Applied Physics Express, 2022, 15, 015501.	1.1	3
9	High-pressure polycrystalline thin-film synthesis and semiconducting property of platinum pernitride. AIP Advances, 2022, 12, .	0.6	1
10	Sn-incorporation effect on thermoelectric properties of Sb-doped Ge-rich Ge <sub>1-x</sub> Si <sub>x</sub> Sn <sub>y</sub> epitaxial layers grown on GaAs(001). Japanese Journal of Applied Physics, 2022, 61, 085502.	0.8	3
11	Impact of Wet Annealing on Ferroelectric Phase Formation and Phase Transition of HfO <sub>2</sub> -ZrO <sub>2</sub> System. ACS Applied Electronic Materials, 2021, 3, 2203-2211.	2.0	6
12	Formation and Characterization of Ge <sub>1-x</sub> Si <sub>x</sub> Sn <sub>y</sub> /Ge Heterojunction Structures for Photovoltaic Cell Application. ECS Meeting Abstracts, 2021, MA2021-01, 2044-2044.	0.0	0
13	Formation and Characterization of Ge <sub>1-x</sub> Si <sub>x</sub> Sn <sub>y</sub> /Ge Heterojunction Structures for Photovoltaic Cell Application. ECS Transactions, 2021, 102, 3-9.	0.3	0
14	Lowering of the Schottky barrier height of metal/n-type 4H-SiC contacts using low-work-function metals with thin insulator insertion. Japanese Journal of Applied Physics, 2021, 60, 075503.	0.8	4
15	No external load measurement strategy for micro thermoelectric generator based on high-performance Si <sub>1-x</sub> Ge <sub>x</sub> Sn <sub>y</sub> film. Journal of Materiomics, 2021, 7, 665-671.	2.8	7
16	Reinforcement of power factor in N-type multiphase thin film of Si <sub>1-x</sub> Ge <sub>x</sub> Sn <sub>y</sub> by mitigating the opposing behavior of Seebeck coefficient and electrical conductivity. Applied Physics Letters, 2021, 119, .	1.5	14
17	(Invited) Thermoelectric Properties of Tin-Incorporated Group-IV Thin Films. ECS Transactions, 2021, 104, 183-189.	0.3	3
18	Silicon-based low-dimensional materials for thermal conductivity suppression: recent advances and new strategies to high thermoelectric efficiency. Japanese Journal of Applied Physics, 2021, 60, SA0803.	0.8	9

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19	(Invited) Thermoelectric Properties of Tin-Incorporated Group-IV Thin Films. ECS Meeting Abstracts, 2021, MA2021-02, 936-936.	0.0	1
20	Improved interface uniformity of epitaxial $\text{HfGe}_2/\text{Ge}(001)$ contact by microfabrication and its electron conduction property. , 2021, , .		1
21	Realizing high thermoelectric performance in p-type $\text{Si}_{1-x-y}\text{Ge}_x\text{Sn}_y$ thin films at ambient temperature by Sn modulation doping. Applied Physics Letters, 2020, 117, .	1.5	16
22	Impact of byproducts formed on a $4\text{H}\text{-SiC}$ surface on interface state density of $\text{Al}_2\text{O}_3/4\text{H}\text{-SiC}(0001)$ gate stacks. Applied Physics Letters, 2020, 116, 222104.	1.5	4
23	Fermi-level pinning at metal/ $4\text{H}\text{-SiC}$ contact induced by $\text{SiC}_x\text{O}_y$ interlayer. Japanese Journal of Applied Physics, 2020, 59, SGGD16.	0.8	7
24	Ferroelectric phase formation for undoped $\text{ZrO}_2$ thin films by wet $\text{O}_2$ annealing. Japanese Journal of Applied Physics, 2020, 59, SMMA04.	0.8	12
25	Saturation of electrically activated Sb concentration in heavily Sb-doped $n\text{-Ge}_{1-x}\text{Sn}_x$ epitaxial layers. Japanese Journal of Applied Physics, 2020, 59, SLLF02.	0.8	3
26	Formation of ultra-thin $\text{Ge}_{1-x}\text{Sn}_x/\text{Ge}_{1-x}\text{Si}_x\text{Sn}_y$ quantum heterostructures and their electrical properties for realizing resonant tunneling diode. Applied Physics Letters, 2020, 117, 232104.	1.5	1
27	Mobility enhancement by mechanical uniaxial stress on $4\text{H}\text{-SiC}$ (0001) lateral metal-oxide-semiconductor field-effect-transistor. Japanese Journal of Applied Physics, 2020, 59, SGGD08.	0.8	6
28	Crystal Growth of Epitaxial $3\text{C}\text{-SiC}$ Thin Film on Si Substrate by Chemical Vapor Deposition using Single Precursor of Vinylsilane. ECS Transactions, 2020, 98, 169-176.	0.3	2
29	(Invited) Heteroepitaxy and Strain Engineering of Germanium-Silicon-Tin Ternary Alloy Semiconductor Thin Films for Energy Band Design. ECS Transactions, 2020, 98, 149-156.	0.3	0
30	(Invited) Heteroepitaxy and Strain Engineering of Germanium-Silicon-Tin Ternary Alloy Semiconductor Thin Films for Energy Band Design. ECS Meeting Abstracts, 2020, MA2020-02, 1714-1714.	0.0	0
31	Crystal Growth of Epitaxial $3\text{C}\text{-SiC}$ Thin Film on Si Substrate by Chemical Vapor Deposition using Single Precursor of Vinylsilane. ECS Meeting Abstracts, 2020, MA2020-02, 1716-1716.	0.0	0
32	Formation and optoelectronic property of strain-relaxed $\text{Ge}_{1-x}\text{Si}_x/\text{Sn}_y/\text{Ge}_{1-x}\text{Sn}_x/\text{Ge}_{1-x}\text{Si}_x$ double heterostructures on a boron-ion-implanted $\text{Ge}(001)$ substrate. Japanese Journal of Applied Physics, 2019, 58, SIIB23.	0.8	5
33	Realizing High Thermoelectric Performance at Ambient Temperature by Ternary Alloying in Polycrystalline $\text{Si}_{1-x-y}\text{Ge}_x\text{Sn}_y$ Thin Films with Boron Ion Implantation. Scientific Reports, 2019, 9, 14342.	1.6	30
34	Fabrication of Porous Silicon using Photolithography and Reactive Ion Etching (RIE). Materials Today: Proceedings, 2019, 13, 92-96.	0.9	4
35	Synthesis of heavily Ga-doped $\text{Si}_{1-x}\text{Sn}_x/\text{Si}$ heterostructures and their valence-band-offset determination. Japanese Journal of Applied Physics, 2019, 58, SAAD02.	0.8	3
36	Influence of Sn precursors on $\text{Ge}_{1-x}\text{Sn}_x$ growth using metal-organic chemical vapor deposition. Japanese Journal of Applied Physics, 2019, 58, SAAD07.	0.8	0

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37	Operation of thin-film thermoelectric generator of Ge-rich poly-Ge <sub>1-x</sub> Sn <sub>x</sub> on SiO <sub>2</sub> fabricated by a low thermal budget process. Applied Physics Express, 2019, 12, 051016.	1.1	6
38	Effect of carbon in Si oxide interlayers of the Al <sub>2</sub> O <sub>3</sub> /4H-SiC structure on interfacial reaction by oxygen radical treatment. Japanese Journal of Applied Physics, 2019, 58, SBBD05.	0.8	3
39	(Invited) Development of Germanium-Tin-Related Semiconductor Heterostructures for Energy Band Design in Electronic and Optoelectronic Applications. ECS Meeting Abstracts, 2019, , .	0.0	0
40	(Invited) Development of Germanium-Tin-Related Semiconductor Heterostructures for Energy Band Design in Electronic and Optoelectronic Applications. ECS Transactions, 2019, 92, 41-46.	0.3	1
41	Effect of N bonding structure in AlON deposited by plasma-assisted atomic layer deposition on electrical properties of 4H-SiC MOS capacitor. Japanese Journal of Applied Physics, 2018, 57, 01AE06.	0.8	5
42	Selective growth of Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial layer on patterned SiO <sub>2</sub> /Si substrate by metal-organic chemical vapor deposition. Japanese Journal of Applied Physics, 2018, 57, 01AC05.	0.8	1
43	Formation of SiC thin films by chemical vapor deposition with vinylsilane precursor. Japanese Journal of Applied Physics, 2018, 57, 01AE08.	0.8	6
44	High n-type Sb dopant activation in Ge-rich poly-Ge <sub>1-x</sub> Sn <sub>x</sub> layers on SiO <sub>2</sub> using pulsed laser annealing in flowing water. Applied Physics Letters, 2018, 112, .	1.5	14
45	Dopant behavior in heavily doped polycrystalline Ge <sub>1-x</sub> Sn <sub>x</sub> layers prepared with pulsed laser annealing in water. Japanese Journal of Applied Physics, 2018, 57, 04FJ02.	0.8	5
46	Epitaxial growth of heavily doped n <sup>+</sup> -Ge layers using metal-organic chemical vapor deposition with in situ phosphorus doping. Thin Solid Films, 2018, 645, 57-63.	0.8	1
47	Formation of epitaxial Hf digermanide/Ge(001) contact and its crystalline properties. Japanese Journal of Applied Physics, 2018, 57, 07MA05.	0.8	4
48	Optoelectronic properties of high-Si-content-Ge <sub>1-x</sub> Si <sub>x</sub> /Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge <sub>1-x</sub> Si <sub>x</sub> double heterostructure. Semiconductor Science and Technology, 2018, 33, 124018.	1.0	7
49	Formation of ultra-low resistance contact with nickel stanogermanide/heavily doped n <sup>+</sup> -Ge <sub>1-x</sub> Sn <sub>x</sub> structure. Semiconductor Science and Technology, 2018, 33, 124001.	1.0	9
50	Growth and electrical properties of in situ Sb-doped Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial layers for source/drain stressor of strained-Ge transistors. Japanese Journal of Applied Physics, 2018, 57, 121303.	0.8	4
51	Improved thermoelectric property of B-doped Si/Ge multilayered quantum dot films prepared by RF magnetron sputtering. Japanese Journal of Applied Physics, 2018, 57, 01AF03.	0.8	5
52	Impact of crystalline structures on the thermal stability and Schottky barrier height of NiGe/Ge contact. Applied Physics Letters, 2018, 113, 253503.	1.5	1
53	Ultra-thin germanium-tin on insulator structure through direct bonding technique. Semiconductor Science and Technology, 2018, 33, 124002.	1.0	5
54	Energy band structure and electrical properties of Ga-oxide/GaN interface formed by remote oxygen plasma. Japanese Journal of Applied Physics, 2018, 57, 06KA05.	0.8	5

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55	(Invited) A New Application of Ge <sub>1-x</sub> Sn <sub>x</sub> : Thermoelectric Materials. ECS Transactions, 2018, 86, 321-328.	0.3	5
56	Alleviation of Fermi level pinning at metal/n-Ge interface with lattice-matched Si <sub>x</sub> Ge <sub>1-x</sub> Sn <sub>y</sub> ternary alloy interlayer on Ge. Japanese Journal of Applied Physics, 2018, 57, 060304.	0.8	4
57	Domain size effects on thermoelectric properties of p-type Ge <sub>0.95</sub> Sn <sub>0.05</sub> layers grown on GaAs and Si substrates. , 2018, , .		0
58	Low thermal budget fabrication of poly-Ge <sub>1-x</sub> Sn <sub>x</sub> thin film thermoelectric generator. , 2018, , .		0
59	Low-temperature crystallization of Ge-rich GeSn layers on Si <sub>3</sub> N <sub>4</sub> substrate. Materials Science in Semiconductor Processing, 2017, 70, 151-155.	1.9	14
60	Modulation of Fermi level pinning position at metal/ n -Ge interface by semimetal Ge <sub>1-x</sub> Sn <sub>x</sub> and Sn interlayers. Materials Science in Semiconductor Processing, 2017, 70, 162-166.	1.9	2
61	Hydrogen-surfactant-mediated epitaxy of Ge <sub>1-x</sub> Sn <sub>x</sub> layer and its effects on crystalline quality and photoluminescence property. Japanese Journal of Applied Physics, 2017, 56, 01AB05.	0.8	3
62	Si <sub>1-x</sub> Ge <sub>x</sub> bulk single crystals for substrates of electronic devices. Materials Science in Semiconductor Processing, 2017, 70, 12-16.	1.9	6
63	EXAFS study of local structure contributing to Sn stability in Si <sub>y</sub> Ge <sub>1-y</sub> zSn <sub>z</sub> . Materials Science in Semiconductor Processing, 2017, 70, 133-138.	1.9	13
64	In situ phosphorus-doped Ge <sub>1-x</sub> Sn <sub>x</sub> layers grown using low-temperature metal-organic chemical vapor deposition. Semiconductor Science and Technology, 2017, 32, 124001.	1.0	0
65	Control of Ge <sub>1-x</sub> Sn <sub>x</sub> Si <sub>x</sub> Sn <sub>y</sub> layer lattice constant for energy band alignment in Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge <sub>1-x</sub> Sn <sub>y</sub> Si <sub>x</sub> Sn <sub>z</sub> Semiconductor Science and Technology, 2017, 32, 104008.	1.0	6
66	Electrical and optical properties improvement of GeSn layers formed at high temperature under well-controlled Sn migration. Materials Science in Semiconductor Processing, 2017, 70, 139-144.	1.9	7
67	(Invited) Growth and Applications of Si <sub>1-x</sub> Sn <sub>x</sub> Thin Films. ECS Transactions, 2017, 80, 253-258.	0.3	5
68	Self-organized lattice-matched epitaxy of Si <sub>1-x</sub> Sn <sub>x</sub> alloys on (001)-oriented Si, Ge, and InP substrates. Applied Physics Letters, 2017, 111, .	1.5	13
69	Evaluation of energy band offset of Si <sub>1-x</sub> Sn <sub>x</sub> semiconductors by numerical calculation using density functional theory. Japanese Journal of Applied Physics, 2017, 56, 04CR10.	0.8	3
70	Formation of epitaxial Hf germanide/Ge contacts for Schottky barrier height engineering. , 2017, , .		1
71	Development of in-situ Sb-Doped Ge <sub>1-x</sub> Sn <sub>x</sub> Epitaxial Layers for Source/Drain Stressor of Strained Ge Transistors. , 2017, , .		0
72	Formation and characterization of Ge <sub>1-x</sub> Si <sub>x</sub> Sn <sub>y</sub> /Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge <sub>1-x</sub> Si <sub>x</sub> Sn <sub>y</sub> double heterostructures with strain-controlled Ge <sub>1-x</sub> Si <sub>x</sub> Sn <sub>y</sub> layers. Materials Science in Semiconductor Processing, 2017, 70, 156-161.	1.9	9

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73	Selective epitaxial growth of Ge <sub>1-x</sub> Sn <sub>x</sub> on Si by using metal-organic chemical vapor deposition. Journal of Crystal Growth, 2017, 468, 614-619.	0.7	3
74	Electrical and optical properties improvement of GeSn layers formed at high temperature under well-controlled Sn migration. Materials Science in Semiconductor Processing, 2017, 57, 48-53.	1.9	16
75	Solid-phase crystallization of Si <sub>1-x</sub> Sn <sub>x</sub> ternary alloy layers and characterization of their crystalline and optical properties. Japanese Journal of Applied Physics, 2017, 56, 01AB02.	0.8	2
76	Effect of GeO <sub>2</sub> deposition temperature in atomic layer deposition on electrical properties of Ge gate stack. Japanese Journal of Applied Physics, 2016, 55, 08PC05.	0.8	6
77	Effects of nitridation for SiO <sub>2</sub> /SiC interface on defect properties near the conduction band edge. Japanese Journal of Applied Physics, 2016, 55, 04ER13.	0.8	3
78	Growth of ultrahigh-Sn-content Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial layer and its impact on controlling Schottky barrier height of metal/Ge contact. Japanese Journal of Applied Physics, 2016, 55, 04EB12.	0.8	6
79	Experimental observation of type-I energy band alignment in lattice-matched Ge <sub>1-x</sub> Sn <sub>x</sub> /Si <sub>1-x</sub> Sn <sub>x</sub> /Ge heterostructures. Applied Physics Letters, 2016, 108, .	1.5	23
80	Density functional study for crystalline structures and electronic properties of Si <sub>1-x</sub> Sn <sub>x</sub> binary alloys. Japanese Journal of Applied Physics, 2016, 55, 08PE04.	0.8	16
81	Low thermal budget n-type doping into Ge(001) surface using ultraviolet laser irradiation in phosphoric acid solution. Applied Physics Letters, 2016, 108, .	1.5	7
82	Analysis of Microscopic Strain and Crystalline Structure in Ge/Ge <sub>1-x</sub> Sn <sub>x</sub> Fine Structures by Using Synchrotron X-ray Microdiffraction. ECS Transactions, 2016, 75, 769-775.	0.3	3
83	Influence of precursor gas on SiGe epitaxial material quality in terms of structural and electrical defects. Japanese Journal of Applied Physics, 2016, 55, 04EJ11.	0.8	0
84	Effect of in situ Sb doping on crystalline and electrical characteristics of n-type Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial layer. Japanese Journal of Applied Physics, 2016, 55, 04EB13.	0.8	10
85	Characterization of Shallow- and Deep-Level Defects in Undoped Ge <sub>1-x</sub> Sn <sub>x</sub> Epitaxial Layers by Electrical Measurements. ECS Journal of Solid State Science and Technology, 2016, 5, P3082-P3086.	0.9	13
86	Characterization of crystallinity of Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial layers grown using metal-organic chemical vapor deposition. Thin Solid Films, 2016, 602, 7-12.	0.8	9
87	Defect and dislocation structures in low-temperature-grown Ge and Ge <sub>1-x</sub> Sn epitaxial layers on Si(110) substrates. Thin Solid Films, 2016, 598, 72-81.	0.8	3
88	Impact of hydrogen surfactant on crystallinity of Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial layers. Japanese Journal of Applied Physics, 2015, 54, 04DH15.	0.8	7
89	Growth of 2 inch Si <sub>0.5</sub> Ge <sub>0.5</sub> bulk single crystals. Japanese Journal of Applied Physics, 2015, 54, 04DH03.	0.8	12
90	Oxygen and germanium migration at low temperature influenced by the thermodynamic nature of the materials used in germanium metal-insulator-semiconductor structures. Applied Physics Letters, 2015, 107, .	1.5	6

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91	Formation of Ge pn-junction diode by phosphorus doping with liquid immersion laser irradiation. , 2015, , .		0
92	Mobility Behavior of Polycrystalline Si <sub>1-x</sub> Ge <sub>x</sub> /Si <sub>1-x</sub> Ge <sub>x</sub> /Si <sub>1-x</sub> Ge <sub>x</sub> /Sn <sub>1-x</sub> Ge <sub>x</sub> /Si <sub>1-x</sub> Ge <sub>x</sub> Grown on Insulators. Transactions of the Materials Research Society of Japan, 2015, 40, 351-354.		
93	Formation, crystalline structure, and optical properties of Ge <sub>1-x</sub> Sn <sub>x</sub> ternary alloy layers. Japanese Journal of Applied Physics, 2015, 54, 04DH08.	0.8	5
94	Reduction of Schottky barrier height at metal/n-Ge interface by introducing an ultra-high Sn content Ge <sub>1-x</sub> Sn <sub>x</sub> interlayer. Applied Physics Letters, 2015, 107, .	1.5	10
95	Growth of Si <sub>1-x</sub> Sn <sub>x</sub> ternary alloy layer on Si(001) substrate and characterization of its crystalline properties. Japanese Journal of Applied Physics, 2015, 54, 08KA11.	0.8	1
96	Epitaxial Ge <sub>1-x</sub> Sn <sub>x</sub> Layers Grown by Metal-Organic Chemical Vapor Deposition Using Tertiary-butyl-germane and Tri-butyl-vinyl-tin. ECS Solid State Letters, 2015, 4, P59-P61.	1.4	10
97	Atom probe tomography study on Ge <sub>1-x</sub> Sn <sub>x</sub> hetero-epitaxial film on Ge substrates. Thin Solid Films, 2015, 592, 54-58.	0.8	1
98	Epitaxial formation of Ni germanide on Ge(0 0 1) substrate by reactive deposition. Solid-State Electronics, 2015, 110, 44-48.	0.8	3
99	Epitaxial growth and crystalline properties of Ge <sub>1-x</sub> Si <sub>x</sub> Sn on Ge(0 0 1) substrates. Solid-State Electronics, 2015, 110, 49-53.	0.8	14
100	Near-infrared light absorption by polycrystalline SiSn alloys grown on insulating layers. Applied Physics Letters, 2015, 106, .	1.5	33
101	Effect of Sn on crystallinity and electronic property of low temperature grown polycrystalline-Si <sub>1-x</sub> Ge <sub>x</sub> Sn layers on SiO <sub>2</sub> . Solid-State Electronics, 2015, 110, 54-58.	0.8	7
102	Growth and applications of GeSn-related group-IV semiconductor materials. Science and Technology of Advanced Materials, 2015, 16, 043502.	2.8	144
103	Influence of interface structure on electrical properties of NiGe/Ge contacts. Japanese Journal of Applied Physics, 2015, 54, 05EA01.	0.8	5
104	Formation of chemically stable GeO <sub>2</sub> on the Ge surface with pulsed metal-organic chemical vapor deposition. Applied Physics Letters, 2015, 106, 062107.	1.5	5
105	Non-uniform depth distributions of Sn concentration induced by Sn migration and desorption during GeSnSi layer formation. Applied Physics Letters, 2015, 106, .	1.5	20
106	Characterization of locally strained Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge fine structures by synchrotron X-ray microdiffraction. Applied Physics Letters, 2015, 106, .	1.5	11
107	High hole mobility tin-doped polycrystalline germanium layers formed on insulating substrates by low-temperature solid-phase crystallization. Applied Physics Letters, 2015, 107, .	1.5	64
108	Heteroepitaxial Growth of Si, Si <sub>1-x</sub> Ge <sub>x</sub> , and Ge-Based Alloy. , 2015, , 1301-1318.		1

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109	Publisher's Note: Impact of hydrogen surfactant on crystallinity of Ge <sub>1-x</sub> Sn <sub>x</sub> epitaxial layers. Japanese Journal of Applied Physics, 2015, 54, 059202.	0.8	10
110	Effect of Sn atoms on incorporation of vacancies in epitaxial Ge <sub>1-x</sub> Sn <sub>x</sub> film grown at low temperature. Applied Physics Express, 2014, 7, 021302.	1.1	11
111	Low temperature growth of SiSn polycrystals with high Sn contents on insulating layers. , 2014, , .		5
112	Impact of Sn incorporation on low temperature growth of polycrystalline-Si <sub>1-x</sub> Ge <sub>x</sub> layers on insulators. , 2014, , .		0
113	Operation of inverter and ring oscillator of ultrathin-body poly-Ge CMOS. Applied Physics Express, 2014, 7, 121302.	1.1	29
114	Importance of Ge surface oxidation with high oxidation rate in obtaining low interface state density at oxide/Ge interfaces. Japanese Journal of Applied Physics, 2014, 53, 08LD02.	0.8	1
115	Reduction of Schottky barrier height for n-type Ge contact by using Sn electrode. Japanese Journal of Applied Physics, 2014, 53, 04EA06.	0.8	12
116	Crystal growth of Sn-related group-IV alloy thin films for advanced Si nanoelectronics. , 2014, , .		0
117	Impact of crystalline structure on electrical property of NiGe/Ge contact. , 2014, , .		0
118	Band alignment at interfaces of amorphous Al <sub>2</sub> O <sub>3</sub> with Ge <sub>1-x</sub> Sn <sub>x</sub> - and strained Ge-based channels. Applied Physics Letters, 2014, 104, 202107.	1.5	4
119	Formation of high-quality oxide/Ge <sub>1-x</sub> Sn <sub>x</sub> interface with high surface Sn content by controlling Sn migration. Applied Physics Letters, 2014, 105, 122103.	1.5	19
120	Interaction of Sn atoms with defects introduced by ion implantation in Ge substrate. Journal of Applied Physics, 2014, 115, .	1.1	4
121	(Invited) Epitaxial Growth of GeSn Layers on (001), (110), and (111) Si and Ge Substrates. ECS Transactions, 2014, 64, 793-799.	0.3	3
122	Formation and crystalline structure of Ni silicides on Si(110) substrate. Japanese Journal of Applied Physics, 2014, 53, 05GA12.	0.8	4
123	Effect of thermal cleaning on formation of epitaxial Ni germanide layer on Ge(110) substrate. Japanese Journal of Applied Physics, 2014, 53, 05GA06.	0.8	1
124	Robustness of Sn precipitation during thermal oxidation of Ge <sub>1-x</sub> Sn <sub>x</sub> on Ge(001). Japanese Journal of Applied Physics, 2014, 53, 08LD04.	0.8	10
125	Formation of high-quality Ge <sub>1-x</sub> Sn <sub>x</sub> layer on Ge(110) substrate with strain-induced confinement of stacking faults at Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge interfaces. Applied Physics Express, 2014, 7, 061301.	1.1	2
126	Interface properties of Al <sub>2</sub> O <sub>3</sub> /Ge structures with thin Ge oxide interfacial layer formed by pulsed metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2014, 53, 08LD03.	0.8	9



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127	Epitaxial formation and electrical properties of Ni germanide/Ge(110) contacts. Thin Solid Films, 2014, 557, 84-89.	0.8	22
128	Importance of control of oxidant partial pressure on structural and electrical properties of Pr-oxide films. Thin Solid Films, 2014, 557, 276-281.	0.8	4
129	Influence of Ge substrate orientation on crystalline structures of Ge <sub>1-x</sub> Sn epitaxial layers. Thin Solid Films, 2014, 557, 159-163.	0.8	14
130	Formation and electrical properties of metal/Ge <sub>1-x</sub> Sn contacts. , 2014, , .		0
131	Large grain growth of Ge-rich Ge <sub>1-x</sub> Sn <sub>x</sub> (x=0.02) on insulating surfaces using pulsed laser annealing in flowing water. Applied Physics Letters, 2014, 104, 061901.	1.5	37
132	Stabilized formation of tetragonal ZrO <sub>2</sub> thin film with high permittivity. Thin Solid Films, 2014, 557, 192-196.	0.8	22
133	Characterization of crystalline structures of SiGe substrate formed by traveling liquidus-zone method for devices with Ge/SiGe structures. Thin Solid Films, 2014, 557, 129-134.	0.8	3
134	Impacts of AlGeO formation by post thermal oxidation of Al <sub>2</sub> O <sub>3</sub> /Ge structure on interfacial properties. Thin Solid Films, 2014, 557, 282-287.	0.8	15
135	Analysis for positions of Sn atoms in epitaxial Ge <sub>1-x</sub> Sn <sub>x</sub> film in low temperature depositions. Thin Solid Films, 2014, 557, 173-176.	0.8	6
136	Formation and characterization of locally strained Ge <sub>1-x</sub> Sn /Ge microstructures. Thin Solid Films, 2014, 557, 164-168.	0.8	6
137	Observation of lattice spacing fluctuation and strain undulation around through-Si vias in wafer-on-wafer structures using X-ray microbeam diffraction. Japanese Journal of Applied Physics, 2014, 53, 05GE03.	0.8	0
138	Understanding of interface structures and reaction mechanisms induced by Ge or GeO diffusion in Al <sub>2</sub> O <sub>3</sub> /Ge structure. Applied Physics Letters, 2013, 103, .	1.5	12
139	Effect of gate metal on chemical bonding state in metal/Pr-oxide/Ge gate stack structure. Solid-State Electronics, 2013, 83, 56-60.	0.8	2
140	Development of epitaxial growth technology for Ge <sub>1-x</sub> Sn alloy and study of its properties for Ge nanoelectronics. Solid-State Electronics, 2013, 83, 82-86.	0.8	23
141	Influence of Sn incorporation and growth temperature on crystallinity of Ge <sub>1-x</sub> Sn <sub>x</sub> layers heteroepitaxially grown on Ge(110) substrates. Thin Solid Films, 2013, 531, 504-508.	0.8	18
142	Epitaxial growth and anisotropic strain relaxation of Ge <sub>1-x</sub> Sn <sub>x</sub> layers on Ge(110) substrates. Solid-State Electronics, 2013, 83, 71-75.	0.8	11
143	Impedance Spectroscopy of GeSn-based Heterostructures. ECS Transactions, 2013, 50, 481-490.	0.3	2
144	Effects of Light Exposure during Plasma Processing on Electrical Properties of GeO <sub>2</sub> /Ge Structures. Japanese Journal of Applied Physics, 2013, 52, 01AC04.	0.8	0

#	ARTICLE	IF	CITATIONS
145	Characterization of Local Strain Structures in Heteroepitaxial Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge Microstructures by Using Microdiffraction Method. ECS Transactions, 2013, 58, 185-192.	0.3	0
146	Interfacial Reaction Mechanisms in Al <sub>2</sub> O <sub>3</sub> /Ge Structure by Oxygen Radical Process. Japanese Journal of Applied Physics, 2013, 52, 04CA08.	0.8	9
147	Increase of Si <sub>0.5</sub> Ge <sub>0.5</sub> Bulk Single Crystal Size as Substrates for Strained Ge Epitaxial Layers. Japanese Journal of Applied Physics, 2013, 52, 04CH02.	0.8	5
148	Liquid-Sn-driven lateral growth of poly-GeSn on insulator assisted by surface oxide layer. Applied Physics Letters, 2013, 103, .	1.5	28
149	Group IV Materials. Series in Optics and Optoelectronics, 2013, , 1-54.	0.0	0
150	Effect of Interfacial Reactions in Radical Process on Electrical Properties of Al <sub>2</sub> O <sub>3</sub> /Ge Gate Stack Structure. Journal of Physics: Conference Series, 2013, 417, 012001.	0.3	3
151	Characterization of Damage of Al <sub>2</sub> O <sub>3</sub> /Ge Gate Stack Structure Induced with Light Radiation during Plasma Nitridation. Japanese Journal of Applied Physics, 2012, 51, 01AJ01.	0.8	1
152	Effect of Gate Metal Electrode on Chemical Bonding State in Metal/Pr-Oxide/Ge Gate Stack Structure. , 2012, , .		0
153	Material Properties and Applications of Ge <sub>1-x</sub> Sn <sub>x</sub> Alloys for Ge Nanoelectronics. , 2012, , .		0
154	Characterization of local strain around trough silicon via interconnects in wafer-on-wafer structures. , 2012, , .		2
155	Epitaxial Growth and Anisotropic Strain Relaxation of Ge <sub>1-x</sub> Sn <sub>x</sub> Layers on Ge(110) Substrates. , 2012, , .		0
156	Electrical Characterization of P-Ge <sub>1-x</sub> Sn <sub>x</sub> /P-Ge and P-Ge <sub>1-x</sub> Sn <sub>x</sub> /n-Ge Heterostructures by Numerical Simulation of Admittance Spectroscopy. , 2012, , .		0
157	Effect of atomic deuterium irradiation on initial growth of Sn and Ge <sub>1-x</sub> Sn <sub>x</sub> on Ge(001) substrates. Applied Surface Science, 2012, 259, 754-757.	3.1	1
158	Crystallinity Improvement of Epitaxial Ge Grown on a Ge(110) Substrate by Incorporation of Sn. Applied Physics Express, 2012, 5, 015501.	1.1	14
159	Homogeneous Si <sub>0.5</sub> Ge <sub>0.5</sub> bulk crystal growth as substrates for strained Ge thin films by the traveling liquidus-zone method. Thin Solid Films, 2012, 520, 3279-3282.	0.8	10
160	In-situ Ga doping of fully strained Ge <sub>1-x</sub> Sn <sub>x</sub> heteroepitaxial layers grown on Ge(001) substrates. Thin Solid Films, 2012, 520, 3206-3210.	0.8	14
161	Improvement of Al <sub>2</sub> O <sub>3</sub> /Ge interfacial properties by O <sub>2</sub> -annealing. Thin Solid Films, 2012, 520, 3397-3401.	0.8	16
162	Low temperature formation of Si <sub>1-x</sub> Ge <sub>x</sub> Sn <sub>y</sub> -on-insulator structures by using solid-phase mixing of Ge <sub>1-z</sub> Sn <sub>z</sub> /Si-on-insulator substrates. Thin Solid Films, 2012, 520, 3288-3292.	0.8	10

#	ARTICLE	IF	CITATIONS
163	Growth of Ge <sub>1-x</sub> Sn <sub>x</sub> heteroepitaxial layers with very high Sn contents on InP(001) substrates. Thin Solid Films, 2012, 520, 3201-3205.	0.8	32
164	Crystalline orientation dependence of electrical properties of Mn Germanide/Ge(1 1 1) and (0 0 1) Schottky contacts. Microelectronic Engineering, 2011, 88, 605-609.	1.1	42
165	Characterization of GeSn materials for future Ge pMOSFETs source/drain stressors. Microelectronic Engineering, 2011, 88, 342-346.	1.1	103
166	Ge <sub>1-x</sub> Sn stressors for strained-Ge CMOS. Solid-State Electronics, 2011, 60, 53-57.	0.8	33
167	Control of strain relaxation behavior of Ge <sub>1-x</sub> Sn <sub>x</sub> buffer layers. Solid-State Electronics, 2011, 60, 84-88.	0.8	11
168	Formation of Ni(Ge <sub>1-x</sub> Sn <sub>x</sub> ) layers with solid-phase reaction in Ni/Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge systems. Solid-State Electronics, 2011, 60, 46-52.	0.8	29
169	Control of interfacial properties of Pr-oxide/Ge gate stack structure by introduction of nitrogen. Solid-State Electronics, 2011, 60, 70-74.	0.8	5
170	Structural Analysis of Si-Based Nanodot Arrays Self-Organized by Selective Etching of SiGe/Si Films. Japanese Journal of Applied Physics, 2011, 50, 08LB11.	0.8	2
171	Analysis of Local Leakage Current of Pr-Oxide Thin Films with Conductive Atomic Force Microscopy. Japanese Journal of Applied Physics, 2011, 50, 04DA08.	0.8	3
172	Control of Interfacial Properties of Al <sub>2</sub> O <sub>3</sub> /Ge Gate Stack Structure Using Radical Nitridation Technique. Japanese Journal of Applied Physics, 2011, 50, 10PE02.	0.8	6
173	Effect of Pr Valence State on Interfacial Structure and Electrical Properties of Pr Oxide/PrON/Ge Gate Stack Structure. Japanese Journal of Applied Physics, 2011, 50, 04DA17.	0.8	2
174	Sn diffusion during Ni germanide growth on Ge <sub>1-x</sub> Sn <sub>x</sub> . Applied Physics Letters, 2011, 99, 211905.	1.5	15
175	Molecular beam deposition of Al <sub>2</sub> O <sub>3</sub> on p-Ge(001)/Ge <sub>0.95</sub> Sn <sub>0.05</sub> heterostructure and impact of a Ge-cap interfacial layer. Applied Physics Letters, 2011, 98, .	1.5	33
176	Self-organization of two-dimensional SiGe nanodot arrays using selective etching of pure-edge dislocation network. Journal of Applied Physics, 2011, 109, 044301-044301-4.	1.1	2
177	(Invited) GeSn Technology: Impact of Sn on Ge CMOS Applications. ECS Transactions, 2011, 41, 231-238.	0.3	8
178	Formation of Palladium Silicide Thin Layers on Si(110) Substrates. Japanese Journal of Applied Physics, 2011, 50, 05EA09.	0.8	4
179	Structural Change during the Formation of Directly Bonded Silicon Substrates. Key Engineering Materials, 2011, 470, 158-163.	0.4	0
180	Characterization of Local Strain around Through-Silicon Via Interconnects by Using X-ray Microdiffraction. Japanese Journal of Applied Physics, 2011, 50, 05ED03.	0.8	8

#	ARTICLE	IF	CITATIONS
181	Effect of Pr Valence State on Interfacial Structure and Electrical Properties of Pr Oxide/PrON/Ge Gate Stack Structure. Japanese Journal of Applied Physics, 2011, 50, 04DA17.	0.8	2
182	Formation of Palladium Silicide Thin Layers on Si(110) Substrates. Japanese Journal of Applied Physics, 2011, 50, 05EA09.	0.8	6
183	Characterization of Local Strain around Through-Silicon Via Interconnects by Using X-ray Microdiffraction. Japanese Journal of Applied Physics, 2011, 50, 05ED03.	0.8	9
184	Structural Analysis of Si-Based Nanodot Arrays Self-Organized by Selective Etching of SiGe/Si Films. Japanese Journal of Applied Physics, 2011, 50, 08LB11.	0.8	7
185	Control of Interfacial Properties of Al <sub>2</sub> O <sub>3</sub> /Ge Gate Stack Structure Using Radical Nitridation Technique. Japanese Journal of Applied Physics, 2011, 50, 10PE02.	0.8	8
186	Low temperature growth of Ge <sub>1-x</sub> Sn buffer layers for tensile-strained Ge layers. Thin Solid Films, 2010, 518, S2-S5.	0.8	69
187	Structural change of direct silicon bonding substrates by interfacial oxide out-diffusion annealing. Thin Solid Films, 2010, 518, S147-S150.	0.8	7
188	Growth and Characterization of Ge <sub>1-x</sub> Sn <sub>x</sub> Layers for High Mobility Tensile-Strained Ge Channels of CMOS Devices. Materials Science Forum, 2010, 654-656, 1788-1791.	0.3	0
189	Tensile-strained Ge and Ge <sub>1-x</sub> Sn <sub>x</sub> layers for high-mobility channels in future CMOS Devices. , 2010, , .		0
190	Formation of Palladium Silicide on Heavily Doped Si(001) Substrates Using Ti Intermediate Layer. Japanese Journal of Applied Physics, 2010, 49, 05FA09.	0.8	5
191	(Invited) Assessment of Ge <sub>1-x</sub> Sn <sub>x</sub> Alloys for Strained Ge CMOS Devices. ECS Transactions, 2010, 33, 529-535.	0.3	13
192	Control of Strain Relaxation Behavior of Ge <sub>1-x</sub> Sn <sub>x</sub> Layers for Tensile Strained Ge Layers. ECS Transactions, 2010, 33, 205-210.	0.3	14
193	Mobility Behavior of Ge <sub>1-x</sub> Sn <sub>x</sub> Layers Grown on Silicon-on-Insulator Substrates. Japanese Journal of Applied Physics, 2010, 49, 04DA10.	0.8	81
194	Silicides. , 2009, , 121-130.		0
195	Characterization and Analyses of Interface Structures in Directly Bonded Si(011)/Si(001) Substrates. Japanese Journal of Applied Physics, 2009, 48, 021208.	0.8	7
196	Mechanical Properties and Chemical Reactions at the Directly Bonded Si-Si Interface. Japanese Journal of Applied Physics, 2009, 48, 011202.	0.8	11
197	Control of Sn Precipitation and Strain Relaxation in Compositionally Step-Graded Ge <sub>1-x</sub> Sn <sub>x</sub> Buffer Layers for Tensile-Strained Ge Layers. Japanese Journal of Applied Physics, 2009, 48, 04C130.	0.8	23
198	Microstructures in directly bonded Si substrates. Solid-State Electronics, 2009, 53, 837-840.	0.8	7

#	ARTICLE	IF	CITATIONS
199	Plasma surface treatment of polymers with inductivity-coupled RF plasmas driven by low-inductance antenna units. <i>Thin Solid Films</i> , 2009, 518, 1006-1011.	0.8	26
200	Novel method to introduce uniaxial tensile strain in Ge by microfabrication of Ge/Si <sub>1-x</sub> Ge structures on Si(0 0 1) substrates. <i>Solid-State Electronics</i> , 2009, 53, 1198-1201.	0.8	6
201	Ferromagnetism and Electronic Structures of Nonstoichiometric Heusler-Alloy $\text{Fe}_{1-x}\text{Mn}_x\text{Ge}$ Grown on Ge(111). <i>Physical Review Letters</i> , 2009, 102, 137204.	2.9	94
202	Influence of interfacial structure on electrical properties of metal/Ge Schottky contacts. , 2009, , .		0
203	Formation of Uniaxial Tensile-strained Ge by Using Micro-patterning of Ge/Si <sub>1-x</sub> Ge/Si Structures. <i>Transactions of the Materials Research Society of Japan</i> , 2009, 34, 305-308.	0.2	0
204	Control of Dislocations and Sn Precipitations for Fabrication of Tensile-strained Ge on Ge <sub>1-x</sub> Sn <sub>x</sub> /Si Buffer Layer. <i>Transactions of the Materials Research Society of Japan</i> , 2009, 34, 301-304.	0.2	0
205	Tensile strained Ge layers on strain-relaxed Ge <sub>1-x</sub> Sn <sub>x</sub> /virtual Ge substrates. <i>Thin Solid Films</i> , 2008, 517, 159-162.	0.8	41
206	Effect of alcohol sources on synthesis of single-walled carbon nanotubes. <i>Applied Surface Science</i> , 2008, 254, 7697-7702.	3.1	19
207	Scanning tunneling microscopy observation of initial growth of Sn and Ge <sub>1-x</sub> Sn <sub>x</sub> layers on Ge(001) substrates. <i>Applied Surface Science</i> , 2008, 254, 6048-6051.	3.1	6
208	Silicide and germanide technology for contacts and gates in MOSFET applications. <i>Thin Solid Films</i> , 2008, 517, 80-83.	0.8	11
209	Dependence of Electrical Characteristics on Interfacial Structure of Epitaxial NiSi <sub>2</sub> /Si Schottky Contacts Formed from Ni/Ti/Si System. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 2402-2406.	0.8	8
210	Epitaxial Ag Layers on Si Substrates as a Buffer Layer for Carbon Nanotube Growth. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 3742-3747.	0.8	0
211	Growth of highly strain-relaxed Ge <sub>1-x</sub> Sn <sub>x</sub> /virtual Ge by a Sn precipitation controlled compositionally step-graded method. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	112
212	Interface and Defect Control for Group IV Channel Engineering. <i>ECS Transactions</i> , 2008, 16, 687-698.	0.3	0
213	Strain relaxation of patterned Ge and SiGe layers on Si(001) substrates. <i>Semiconductor Science and Technology</i> , 2007, 22, S132-S136.	1.0	11
214	Silicide and Germanide Technology for Contacts and Metal Gates in MOSFET Applications. <i>ECS Transactions</i> , 2007, 11, 197-205.	0.3	3
215	Impact of Pt Incorporation on Thermal Stability of NiGe Layers on Ge(001) Substrates. , 2007, , .		5
216	Growth and structure evaluation of strain-relaxed Ge <sub>1-x</sub> Sn <sub>x</sub> buffer layers grown on various types of substrates. <i>Semiconductor Science and Technology</i> , 2007, 22, S231-S235.	1.0	70

#	ARTICLE	IF	CITATIONS
217	Ni-Silicide/Si and SiGe(C) Contact Technology for ULSI Applications. , 2006, , .		0
218	Electrical properties of epitaxial NiSi <sub>2</sub> /Si contacts with extremely flat interface formed in Ni/Ti/Si(001) system. Microelectronic Engineering, 2006, 83, 2272-2276.	1.1	13
219	Local strain in SiGe/Si heterostructures analyzed by X-ray microdiffraction. Thin Solid Films, 2006, 508, 128-131.	0.8	27
220	Control of misfit dislocations in strain-relaxed SiGe buffer layers on SOI substrates. Thin Solid Films, 2006, 508, 147-151.	0.8	6
221	Initial Growth Process of TiN Films in Ultrahigh-Vacuum Rapid Thermal Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, 49-53.	0.8	5
222	Ni silicide and germanide technology for contacts and metal gates in MOSFET applications. , 2006, , .		0
223	Scanning Tunneling Microscopy Study on the Reaction of Oxygen with Clean Ge(001) Surfaces. ECS Transactions, 2006, 3, 1197-1203.	0.3	1
224	Dislocation Morphology and Crystalline Mosaicity in Strain-Relaxed SiGe Buffer Layers on SOI. IEEE Transactions on Electronics, Information and Systems, 2006, 126, 1083-1087.	0.1	0
225	Initial growth behaviors of SiGeC in SiGe and C alternate deposition. Materials Science in Semiconductor Processing, 2005, 8, 5-9.	1.9	5
226	Growth and characterization of strain-relaxed SiGe buffer layers on Si(001) substrates with pure-edge misfit dislocations. Materials Science in Semiconductor Processing, 2005, 8, 131-135.	1.9	17
227	Improvement in NiSi/Si contact properties with C-implantation. Microelectronic Engineering, 2005, 82, 479-484.	1.1	55
228	Analysis of Microstructures in SiGe Buffer Layers on Silicon-on-Insulator Substrates. Japanese Journal of Applied Physics, 2005, 44, 7356-7363.	0.8	5
229	Low-Temperature Formation of Epitaxial NiSi <sub>2</sub> Layers with Solid-Phase Reaction in Ni/Ti/Si(001) Systems. Japanese Journal of Applied Physics, 2005, 44, 2945-2947.	0.8	30
230	Pure-edge dislocation network for strain-relaxed SiGe/Si(001) systems. Applied Physics Letters, 2005, 86, 2219-2221.	1.5	58
231	Influence of Structural Variation of Ni Silicide Thin Films on Electrical Property for Contact Materials. Japanese Journal of Applied Physics, 2004, 43, 1896-1900.	0.8	18
232	Interfacial reaction and electrical properties in Ni/Si and Ni/SiGe(C) contacts. Applied Surface Science, 2004, 224, 215-221.	3.1	36
233	Influence of Si <sub>1-x</sub> Ge <sub>x</sub> interlayer on the initial growth of SiGeC on Si(1 0 0). Applied Surface Science, 2004, 224, 117-121.	3.1	3
234	Strain-relaxation mechanisms of SiGe layers formed by two-step growth on Si(0 0 1) substrates. Applied Surface Science, 2004, 224, 104-107.	3.1	16

#	ARTICLE	IF	CITATIONS
235	Dislocation structures and strain-relaxation in SiGe buffer layers on Si (0 0 1) substrates with an ultra-thin Ge interlayer. Applied Surface Science, 2004, 224, 108-112.	3.1	13
236	Influence of C incorporation on the initial growth of epitaxial NiSi <sub>2</sub> on Si(100). Applied Surface Science, 2004, 237, 150-155.	3.1	1
237	Development of Ni/Al and Ni/Ti/Al ohmic contact materials for p-type 4H-SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 98, 286-293.	1.7	72
238	Effect of Al interlayers on two-step epitaxial growth of CoSi <sub>2</sub> on Si(1 0 0). Applied Surface Science, 2003, 216, 174-180.	3.1	2
239	High resolution-high energy x-ray photoelectron spectroscopy using third-generation synchrotron radiation source, and its application to Si-high k insulator systems. Applied Physics Letters, 2003, 83, 1005-1007.	1.5	351
240	Scanning Tunneling Microscopy of Initial Nitridation Processes on Oxidized Si(100) Surface with Radical Nitrogen. Japanese Journal of Applied Physics, 2003, 42, 1966-1970.	0.8	2
241	Electrical Properties and Solid-Phase Reactions in Ni/Si(100) Contacts. Japanese Journal of Applied Physics, 2002, 41, 2450-2454.	0.8	36
242	CoAl Ohmic Contact Materials with Improved Surface Morphology for p-Type 4H-SiC. Materials Science Forum, 2002, 389-393, 885-888.	0.3	6
243	Low Resistance TiAl Ohmic Contacts with Multi-Layered Structure for p-Type 4H-SiC. Materials Transactions, 2002, 43, 1684-1688.	0.4	43
244	Interfacial reactions of Ti/ and Zr/Si <sub>1-x</sub> Ge <sub>x</sub> /Si contacts with rapid thermal annealing. Thin Solid Films, 2000, 373, 73-78.	0.8	10
245	Dependence of contact resistivity on impurity concentration in Co/Si systems. Applied Surface Science, 2000, 159-160, 149-153.	3.1	1
246	Conductance Oscillations in Hopping Conduction Systems Fabricated by Focused Ion Beam Implantation. Japanese Journal of Applied Physics, 1997, 36, 4046-4048.	0.8	3
247	Microscopic Structure of Directly Bonded Silicon Substrates. Key Engineering Materials, 0, 470, 164-170.	0.4	1
248	Strained Ge and Ge <sub>1-x</sub> Sn <sub>x</sub> ; Technology for Future CMOS Devices. Key Engineering Materials, 0, 470, 146-151.	0.4	1
249	Defects Induced by Reactive Ion Etching in Ge Substrate. Advanced Materials Research, 0, 896, 241-244.	0.3	1
250	Visualization of local strain in 4H-SiC trench metal-oxide-semiconductor field-effect transistor using synchrotron nanobeam X-ray diffraction. Japanese Journal of Applied Physics, 0, , .	0.8	0